

### **Amendments to the Claims**

This listing of claims will replace all prior versions, and listings, of claims in the application:

#### **Listing of Claims**

Claim 1 (currently amended): A semiconductor device comprising:

a semiconductor substrate having source/drain regions spaced from each other;

a gate pattern disposed on the semiconductor substrate between the source/drain regions, said gate pattern having opposite side walls;

L-shaped spacers each including a vertical portion covering a respective one of the side walls of the gate pattern, and a lateral portion extending laterally from the bottom of the vertical portion over a respective one of the source/drain regions, whereby the bottom surface of each L-shaped spacer at the underside of the lateral portion faces the substrate; and

support portions interposed between said L-shaped spacers and the gate pattern, said support portions supporting said L-shaped spacers such that the lateral portion of each of the L-shaped spacers is spaced above the source/drain region over which the L-shaped spacer extends, and wherein an air gap exists between the lateral portion of each of the L-shaped spacers and the source/drain region over which the lateral portion extends, the entire bottom surface of the L-shaped spacer being exposed and delimiting the air gap.

Claim 2 (original): The semiconductor device according to claim 1, wherein the source/drain region comprises a lightly-doped source/drain region over which the lateral portion of one of said L-shaped spacers extends, and highly-doped source/drain region disposed laterally of the lateral portion of the L-shaped spacer.

Claim 3 (original): The semiconductor device according to claim 1, wherein said L-shaped spacers comprise an oxide layer.

Claim 4 (original): The semiconductor device according to claim 1, wherein said support portions comprise a polysilicon layer or a nitride layer.

Claim 5 (currently amended): The semiconductor device according to claim 1, and further comprising a buffer insulating layer interposed between said gate pattern and said support portions.

Claims 6 – 20 (canceled)

Claim 21 (new): A semiconductor device comprising:  
a semiconductor substrate having source/drain regions spaced from each other;  
a gate pattern disposed on the semiconductor substrate between the source/drain regions, said gate pattern having opposite side walls;

L-shaped spacers each including a vertical portion covering a respective one of the side walls of the gate pattern, and a lateral portion extending laterally from the bottom of the vertical portion over a respective one of the source/drain regions; and

support portions interposed between said L-shaped spacers and the gate pattern, said support portions supporting said L-shaped spacers such that the lateral portion of each of the L-shaped spacers is spaced above the source/drain region over which the L-shaped spacer extends, and wherein an air gap exists between the lateral portion of each of the L-shaped spacers and the source/drain region over which the lateral portion extends, and

wherein the source/drain regions include lightly-doped source drain regions, respectively, and the gate pattern and said support portions are disposed over a region of the substrate confined between the lightly-doped source/drain regions.

Claim 22 (new): The semiconductor device according to claim 21, wherein said source/drain regions include highly-doped source/drain regions disposed laterally of the lateral portions of the L-shaped spacers, respectively.

Claim 23 (new): The semiconductor device according to claim 21, wherein said L-shaped spacers comprise an oxide layer.

Claim 24 (new): The semiconductor device according to claim 21, wherein said support portions comprise a polysilicon layer or a nitride layer.

Claim 25 (new): The semiconductor device according to claim 1, and further comprising a buffer insulating layer interposed between said gate pattern and said support portions.